

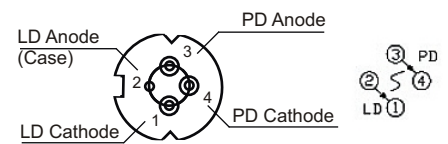
FP-Laser Diode 1310 nm

Features of Diode

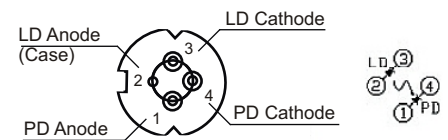
- Uncooled laser diode with MQW structure
- 5 mW CW operation at -40 to 85 °C
- High temperature operation without active cooling
- Hermetically sealed active component
- Built-in InGaAs monitor photodiode
- Complies with Telcordia (Bellcore) GR-468-CORE
- TO-18 packaging with a flat window cap or ball lens cap



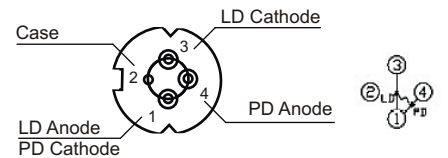
PINOUT (Bottom View)



Type A



Type B



Type D

Absolute maximum ratings

Parameter	Min.	Max.
Storage temperature	-40 °C	85 °C
Operating temperature	-40 °C	85 °C
Laser continuous forward current		150 mA
Laser reverse voltage		2.0 V
PD reverse voltage		10 V

Electrical-optical characteristics

Parameter Laser Diode	Test Condition	Min.	Typ.	Max.
Wavelength		1290 nm	1310 nm	1330 nm
Threshold current	CW, $P_o = 5$ mW		10 mA	15 mA
Laser forward voltage	CW, $P_o = 5$ mW		1.2 V	1.5 V
Rise and fall time	10%-90%			0.5 ns
Parameter Monordiode	Test Condition	Min.	Typ.	Max.
Monitor current	CW, $P_o = 5$ mW, $V_{RPD} = 2$ V	100 μ A		
Dark current	$V_{RPD} = 5$ V			0.1 μ A
PD capacitance	$V_{RPD} = 5$ V, $f = 1$ MHz		6 pF	15 pF
Parameter Receptacle		Min.	Typ.	Max.
Optical output power (type A)	Singlemode 9/125 μ m fiber		1700 μ W	
	Multimode 50/125 μ m fiber		3500 μ W	
Possible receptacle (type A)	ST1, ST2, ST4, P2, LC, SC, FC1, FC2, Fiberdip, SMA1 ¹⁾ , SMA2 ¹⁾			

Compliant with RoHS-requirements (2002/95/EG vom 27.01.2003)